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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/719,926	11/21/2003	Yuji Takaoka	09792909-5767	3342
26263	7590 07/07/2004		EXAMINER	
SONNENSC	HEIN NATH & ROSEN	BEREZNY,	BEREZNY, NEMA O	
P.O. BOX 061	080		ART UNIT	
WACKER DR	WACKER DRIVE STATION, SEARS TOWER			PAPER NUMBER
CHICAGO, IL 60606-1080			2813	

DATE MAILED: 07/07/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/719,926	TAKAOKA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Nema O Berezny	2813				
The MAILING DATE f this communication app ars on th cov r sh et with the correspondence addr ss Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply of the No period for reply is specified above, the maximum statutory period was reply reply to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be timed within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on	_··					
2a) This action is FINAL . 2b) ☑ This	action is non-final.					
·	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4)⊠ Claim(s) <u>17-21</u> is/are pending in the application 4a) Of the above claim(s) is/are withdray 5)□ Claim(s) is/are allowed. 6)⊠ Claim(s) <u>17-21</u> is/are rejected. 7)□ Claim(s) is/are objected to. 8)□ Claim(s) are subject to restriction and/or	wn from consideration.					
Application Papers						
9) The specification is objected to by the Examine 10) The drawing(s) filed on 21 November 2003 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex	re: a) \square accepted or b) \square object drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).				
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 11212003.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:					

Application/Control Number: 10/719,926

Art Unit: 2813

DETAILED ACTION

Specification

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The specification is objected to as failing to provide proper antecedent basis for the claimed subject matter. See 37 CFR 1.75(d)(1) and MPEP § 608.01(o). Correction of the following is required: claim 19 claims a substrate comprising a semiconductor wafer. However, the instant spec discloses only a silicon wafer.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 17-18 and 20-21 are rejected under 35 U.S.C. 102(e) as being anticipated by Eichelberger (6,159,767). Eichelberger discloses a method of fabrication of a semiconductor device, comprising the steps of: die bonding of a plurality of semiconductor chips (Figs.5d-5h el.102) on a substrate (el.140); forming of an insulation film (el.106) on said substrate, wherein said plurality of semiconductor chips is incrusted

Page 3

Art Unit: 2813

in said insulation film (Fig.5e); forming of a connection hole reaching a semiconductor chip of said plurality of semiconductor chips on said insulation film (Fig.5e); and forming of wiring (el.110) on said insulation film, wherein said wiring is connected to said semiconductor chip through said connection hole (Fig.5e) [claim 17]. Eichelberger also discloses further comprising the steps of: forming of an upper layer insulation film (el.150) on said insulation film, wherein said upper layer insulation film covers said wiring; forming of a connection hole reaching said wiring, on said upper layer insulation film (Fig.5f); and forming of an electrode (no #) on said upper layer insulation film, wherein said electrode is connected to said wiring through said connection hole (Fig.5f; col.11 lines 30-33) [claim 18]; wherein said die bonding of said plurality of semiconductor chips on said substrate comprises die bonding of each said semiconductor chip on said substrate, wherein each said semiconductor chip is set so as to float on an adhesive resin (el.142) applied on said substrate (Fig.5d) [claim 20]; and wherein after said step of forming said wiring, said substrate is removed from said semiconductor chip and said insulation film (Fig.5g; col.11 lines 50-51) [claim 21].

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Application/Control Number: 10/719,926 Page 4

Art Unit: 2813

Claim 19 is rejected under 35 U.S.C. 103(a) as being unpatentable over Eichelberger as applied to claim 17 above, and further in view of Gates (5,489,554). Eichelberger does not disclose a substrate comprising a silicon wafer. However, Eichelberger would look to one such as Gates for a wafer with a compatible coefficient of thermal expansion because Gates discloses wherein said substrate is a silicon wafer (Fig.1a-1b; col.3 lines 31-34). Therefore, it would have been obvious to a person of ordinary skill in the art at the time of the invention to use the silicon wafer of Gates with the method of Eichelberger in order to provide a support substrate with a similar coefficient of thermal expansion as that of the semiconductor device layer (Gates - col.4 lines 1-3).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Nema O Berezny whose telephone number is (571) 272-1686. The examiner can normally be reached on M-F 8:30-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/719,926

Art Unit: 2813

Page 5

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NB

Nema Berezny